



**EUROSIO 2010 CONFERENCE ANNOUNCES KEYNOTE PRESENTERS  
AND TECHNICAL PROGRAM**

*International SOI event will be held in Grenoble, France on January 25-27, 2010*

GRENOBLE, France—January 12, 2010—EUROSIO, an international forum for promoting high-level scientific research and exchanges between research groups and industrial partners involved in silicon-on-insulator (SOI) activities all over the world, today announced the final program of its 6<sup>th</sup> annual conference, which will be held on January 25-27, 2010 in Grenoble, France. Horacio Mendez, executive director of the SOI Industry Consortium will kick off the conference with his plenary talk on “SOI for the Next 5 Years”; Professor Krishna Saraswat from Stanford University will present a plenary talk on “Germanium Integration on Silicon for High performance FETs and Optical Interconnects.” In addition, 55 presentations have been selected for the technical program. World-class experts will give a five-session SOI tutorial entitled “Exploring New Routes with SOI” on the first day.

Key to EUROSOI’s continued success is the exceptional synergy between fundamental science, applied physics, technology and SOI application-oriented developments. Following the tradition of previous meetings, EUROSOI’10 will be a lively experience featuring oral and poster sessions, keynote presentations, a training course as well as room for informal discussions. EUROSOI covers recent progress in SOI, including: (1) Synthesis of advanced SOI wafers (Ge, SiGe and strained layers, SOI heterostructures); (2) Materials evaluation, properties of ultra-thin films and buried oxides; (3) SOI MOSFETs: characterization, modeling and simulations, parameter extraction, reliability issues; (4) High performance and Low Power CMOS, (5) New domain of applications such as memories, sensors and MEMS; (6) Innovative devices: multiple-gates, tunneling transistors, nanowires, etc.

“SOI is entering a new era,” notes conference co-chair Sorin Cristoloveanu, a professor and researcher at the IMEP research and education institute in Grenoble. Co-chair Olivier Faynot from CEA-Leti adds: “Originally used for high-performance technologies dedicated to the microprocessors market and gaming, it is now moving to other markets such as the Low Power and mobile applications, memory and power devices. These new markets offer huge opportunities, particularly with respect to the inherent energy savings of SOI, which will enable us to make a smooth transition to a greener world.”

This year's EUROSUI conference is situated in the beautiful city of Grenoble, which can be considered the SOI capital of the world. Research on the fundamentals of SOI has been conducted in this area for more than 30 years by several local institutes including CEA-Leti (Applied research laboratory operated by the Technology Research Directorate of the French Atomic Energy Commission) and CNRS (National Council for Scientific Research), as well as the INP Grenoble University. It is also the home to Soitec, the world's leading manufacturer of SOI wafers.

EUROSUI'10 will be held on the MINATEC innovation campus, an international center for micro and nanotechnologies, which is home to 2400 researchers, 1200 students, and 600 technology transfer experts.

**About EUROSUI:**

EUROSUI 2010 is sponsored by the European Union, Soitec, INP Grenoble and CEA-Léti. For more information about EUROSUI 2010, registration and technical programs please visit: <http://grenoble2010.eurosoi.org/>

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